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(54) Title: COMPOSITION AND METHOD FOR POLISHING BULK SILICON

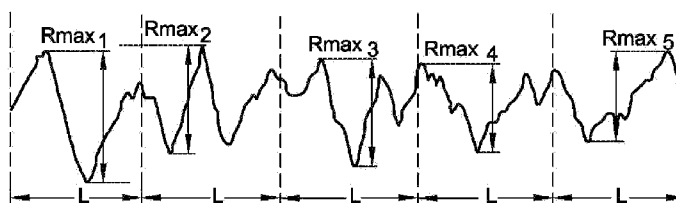


FIG. 1

(57) Abstract: The invention provides a polishing composition comprising (a) silica, (b) one or more compounds that increase the removal rate of silicon, (c) one or more tetraalkylammonium salts, and (d) water, wherein the polishing composition has a pH of 7 to 11. The invention further provides a method of polishing a substrate with the polishing composition.